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a ferroelectric thin film constructed of at least three layers including a lowermost layer, an uppermost layer and an intermediate layer located between the lowermost layer and the uppermost layer, said lowermost layer being directly laminated on another side of said lower electrode; and

an upper electrode directly laminated, on one side, to said uppermost layer, wherein a crystal grain of at least one of the lowermost layer and the uppermost layer is smaller than a crystal grain of the intermediate layer.

28. (Amended) A semiconductor device having a ferroelectric capacitor comprising:

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a lower electrode laminated on one side to a substrate;
a ferroelectric thin film constructed of at least three layers including a lowermost layer, an uppermost layer and an intermediate layer located between the lowermost layer and the uppermost layer, said lowermost layer being directly laminated on another side of said lower electrode; and

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an upper electrode directly laminated, on one side, to said uppermost layer, wherein
a crystalline nucleus density of the lowermost layer is higher than those of the other layers.

Please add the following new claims 30-36.

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--30. (New) A semiconductor device having a ferroelectric capacitor comprising:
a lower electrode laminated on a substrate;

a ferroelectric thin film laminated on the lower electrode and constructed of five layers including a lowermost layer, an uppermost layer and three intermediate layers located between the lowermost layer and the uppermost layer; and
an upper electrode laminated on the ferroelectric thin film,
wherein a crystal grain of at least one of the lowermost layer and the uppermost layer is smaller than a crystal grain of the intermediate layers.

31. (New) A semiconductor device as claimed in claim 30, wherein
a crystal grain of the lowermost layer and a crystal grain of the uppermost layer is smaller than a crystal grain of the intermediate layers.

32. (New) A semiconductor device having a ferroelectric capacitor comprising:
a lower electrode laminated on a substrate;
a ferroelectric thin film laminated on the lower electrode, constructed of five layers including a lowermost layer, an uppermost layer and three intermediate layers located between the lowermost layer and the uppermost layer; and
an upper electrode laminated on the ferroelectric thin film,
wherein
a crystalline nucleus density of the lowermost layer is higher than those of the other layers.

33. (New) A semiconductor device as claimed in claim 30, said lowermost layer of said ferroelectric thin film being directly laminated on the lower electrode.

34. (New) A semiconductor device as claimed in claim 32, said lowermost layer of said ferroelectric thin film being directly laminated on the lower electrode.

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35. (New) A semiconductor device as claimed in claim 30, the upper electrode being directly laminated on said uppermost layer of said ferroelectric thin film.

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at.
36. (New) A semiconductor device as claimed in claim 32, the upper electrode being directly laminated on said uppermost layer of said ferroelectric thin film.--
